Unit: mm

TOSHIBA Multi-Chip Transistor Silicon NPN / PNP Epitaxial Type

# **TPC6901A**

# High-Speed Switching Applications MOS Gate Drive Applications

NPN and PNP transistors are mounted on a compact and slim package.

• High DC current gain : NPN hFE = 400 to 1000

: PNP h<sub>FE</sub> = 200 to 500

Low collector-emitter saturation voltage

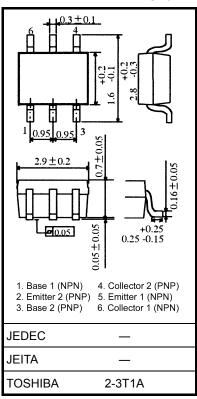
: NPN  $V_{CE (sat)} = 0.17 \text{ V (max)}$ : PNP  $V_{CE (sat)} = -0.23 \text{ V (max)}$ 

• High-speed switching : NPN t<sub>f</sub> = 85 ns (typ.)

: PNP  $t_f = 70 \text{ ns (typ.)}$ 

### **Absolute Maximum Ratings (Ta = 25°C)**

Characteristics			Cumbal	Rating		Unit	
			Symbol	NPN	PNP	Offic	
Collector-base voltage			$V_{CBO}$	100	-50	V	
Collector-emitter voltage			V <sub>CEX</sub>	80	-50	V	
Collector-emitter voltage			V <sub>CEO</sub>	50	-50	V	
Emitter-base voltage			V <sub>EBO</sub>	7	-7	V	
Calla atau ayumant		DC (Note 1)	IC	1.0	-0.7	Α	
Collector current		Pulse (Note 1)	I <sub>CP</sub>	5.0	-5.0	Α	
Base current			ΙΒ	0.1	-0.1	Α	
Collector power dissipation (t=10 s)	Single-device operation		P <sub>C</sub> (Note 2)	500		mW	
Collector power dissipation (DC)	Single-device operation		P <sub>C</sub> (Note 2)	400		mW	
	Single-device value at dual operation		P <sub>C</sub> (Note 2)	330			
Thermal resistance, junction to ambient (t=10 s)	Single-device operation		R <sub>th (j-a)</sub> (Note 2)	250		°C/W	
Thermal resistance, junction to ambient (DC)	Single-device operation		R <sub>th (j-a)</sub> (Note 2)	312		°C/W	
	Single-device value at dual operation		R <sub>th (j-a)</sub> (Note 2)	378			
Junction temperature			Tj	150		°C	
Storage temperature range			T <sub>stg</sub>	-55 to 150		°C	



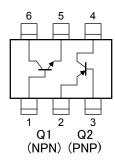
Weight: 0.011 g (typ.)

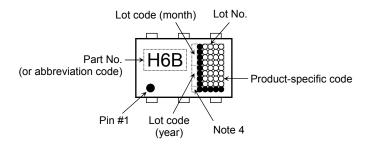
- Note 1: Please use devices on condition that the junction temperature is below 150°C.
- Note 2: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm<sup>2</sup>)
- Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

# **Circuit Configuration**

# Marking





Note 4: A dot marking identifies the indication of product Labels. [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

# **Electrical Characteristics (Ta = 25°C): NPN**

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	$V_{CB} = 100 \text{ V}, I_{E} = 0$	_	_	100	nA
Emitter cut-off current		I <sub>EBO</sub>	$V_{EB} = 7 \text{ V, } I_{C} = 0$	_	_	100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = 10 \text{ mA}, I_B = 0$	50	_	_	٧
DC current gain		h <sub>FE</sub> (1)	V <sub>CE</sub> = 2 V, I <sub>C</sub> = 0.1 A	400	_	1000	
		h <sub>FE</sub> (2)	$V_{CE} = 2 \text{ V}, I_{C} = 0.3 \text{ A}$	200	_	_	
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	$I_C = 300 \text{ mA}, I_B = 6 \text{ mA}$	_	_	0.17	٧
Base-emitter saturation voltage		V <sub>BE (sat)</sub>	$I_C = 300 \text{ mA}, I_B = 6 \text{ mA}$	_	_	1.10	٧
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f = 1 MHz	_	5	_	pF
Switching time	Rise time	t <sub>r</sub>	See Figure 1 circuit diagram.	_	35	_	
	Storage time	t <sub>stg</sub>	$V_{CC} \approx 30 \text{ V}, R_L = 100 \Omega$	_	680	_	ns
	Fall time	t <sub>f</sub>	I <sub>B1</sub> = I <sub>B2</sub> = 10 mA	_	85	_	

# Electrical Characteristics (Ta = 25°C): PNP

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current		I <sub>CBO</sub>	$V_{CB} = -50 \text{ V}, I_E = 0$	_	_	-100	nA
Emitter cut-off current		I <sub>EBO</sub>	$V_{EB} = -7 \text{ V}, I_{C} = 0$	_	_	-100	nA
Collector-emitter breakdown voltage		V (BR) CEO	$I_C = -10 \text{ mA}, I_B = 0$	-50	_	_	V
DC current gain		h <sub>FE</sub> (1)	$V_{CE} = -2 \text{ V}, I_{C} = -0.1 \text{ A}$	200	_	500	
		h <sub>FE</sub> (2)	$V_{CE} = -2 \text{ V}, I_{C} = -0.3 \text{ A}$	125	_	_	
Collector-emitter saturation voltage		V <sub>CE</sub> (sat)	$I_C = -300 \text{ mA}, I_B = -10 \text{ mA}$	_	_	-0.23	V
Base-emitter saturation voltage		V <sub>BE</sub> (sat)	$I_C = -300 \text{ mA}, I_B = -10 \text{ mA}$	_	_	-1.10	V
Collector output capacitance		C <sub>ob</sub>	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz	_	8	_	pF
Switching time	Rise time	t <sub>r</sub>	See Figure 2 circuit diagram.	_	60	_	
	Storage time	t <sub>stg</sub>	$V_{CC} \approx -30 \text{ V}, R_L = 100 \Omega$	_	280	_	ns
	Fall time	t <sub>f</sub>	$I_{B1} = I_{B2} = 10 \text{ mA}$	_	70	_	

VCC I<sub>B1</sub> I<sub>B2</sub> I<sub>B2</sub> Output Duty cycle < 1%

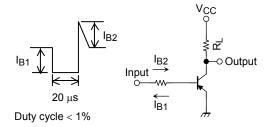
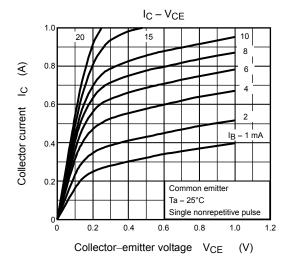
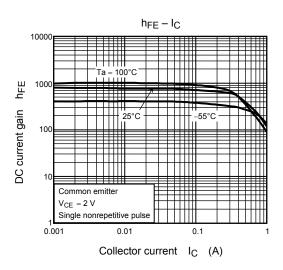


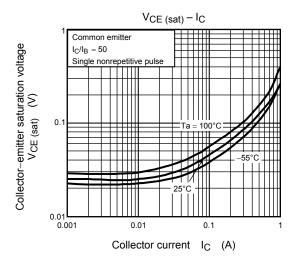
Figure 1 Switching Time Test Circuit & Figure 2 Switching Time Test Circuit & Timing Chart (NPN) Timing Chart (PNP)

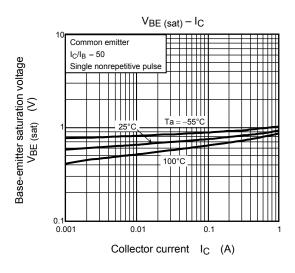
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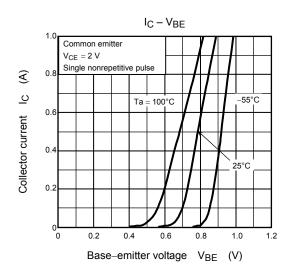
#### **NPN**

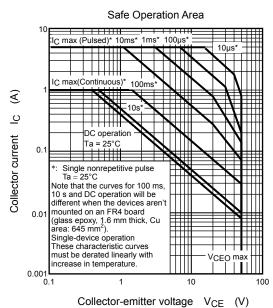






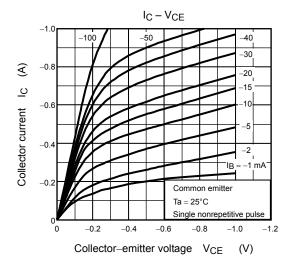


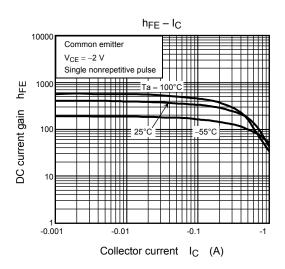


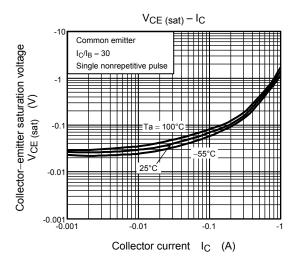


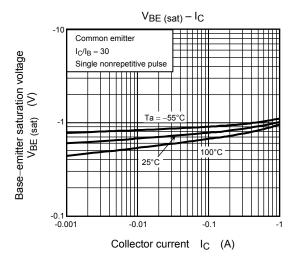
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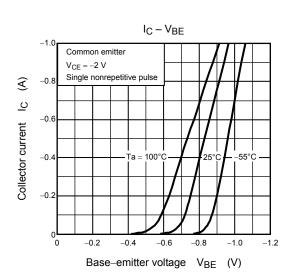
#### **PNP**

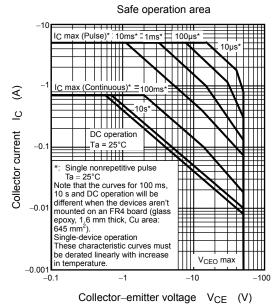






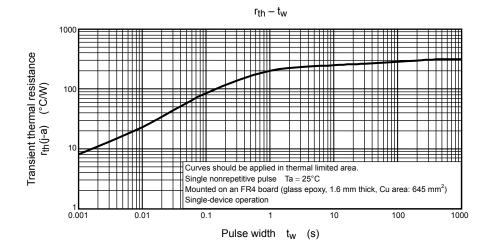


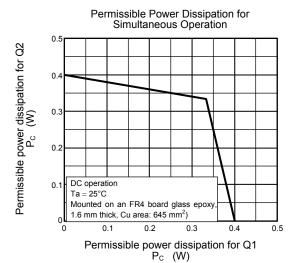




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#### Common





Collector power dissipation at the single-device operation is 0.4W.

Collector power dissipation at the single-device value at dual operation is 0.33W.

Collector power dissipation at the dual operation is set to 0.66W.

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